



SIE864DF-T1-GE3 Information



For Reference Only

Part Number SIE864DF-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 45A POLARPAK **Package** 10-PolarPAK? (U)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









SIE864DF-T1-GE3 Specifications

Manufacturer Part NumberSIE864DF-T1-GE3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage10-PolarPAK? (U)SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250µAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1510pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 10-PolarPAK? (U) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 45A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1510pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Manufacturer Part Number	SIE864DF-T1-GE3
Package 10-PolarPAK? (U) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 45A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1510pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Manufacturer	Vishay Siliconix
Package 10-PolarPAK? (U) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 45A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1510pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Category	Discrete Semiconductor Products
Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 45A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1510pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1510pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)	Package	10-PolarPAK? (U)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1510pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)	Series	TrenchFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1510pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature Supplier Device Package 10-PolarPAK? (U) Package / Case 45A (Tc) 45A (Tc	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Supplier Device Package 10-PolarPAK? (U) 4.5V, 10V 5.6μΑ 5.2ν (250μΑ 5.2ν (Τα), 25V (Τα) 5.6 mOhm @ 20A, 10V 5.6μοτία με το με	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package 10-PolarPAK? (U) 2V @ 250μA 38nC @ 10V 1510pF @ 15V ±20V FET (F at 15V - - - Sufface Mount Supplier Device Package 10-PolarPAK? (U)	Current - Continuous Drain (Id) @ 25°C	45A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1510pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.2W (Ta), 25W (Tc) Sometimal Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) S.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
FET Feature - Power Dissipation (Max) 5.2W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Input Capacitance (Ciss) (Max) @ Vds	1510pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.6 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5.6 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (U)Package / Case10-PolarPAK? (U)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Power Dissipation (Max)	5.2W (Ta), 25W (Tc)
Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Rds On (Max) @ Id, Vgs	5.6 mOhm @ 20A, 10V
Supplier Device Package 10-PolarPAK? (U) Package / Case 10-PolarPAK? (U)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 10-PolarPAK? (U)	Mounting Type	Surface Mount
	Supplier Device Package	10-PolarPAK? (U)
Report errors?	Package / Case	10-PolarPAK? (U)
		Report errors?

SIE864DF-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIE864DF-T1-GE3 Payment Methods



















SIE864DF-T1-GE3 Shipping Methods













If you have any question about SIE864DF-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com